GaOF

1963

GaOF

GaSF

Gallium chalcogenide halides. Harry Hahn and Hartmut Katscher (Univ. Wuerzburg, Ger.). *Z. Anorg. Allgem. Chem.* 321, 85–93(1963). The compds. GaOX and GaSX (X = F, Cl, Br, or I), and GaSeX and GaTeX (X = Cl, Br, or I only) were prepd. by heating appropriate mixts. of the elements, Ga chalcogenides, and GaX_3. Optimum prepn. temps. ranged from 210 to 345°; even at these temps. considerable decompn. occurred. GaOF and GaSF, which are chem. inert, did not decomp. at 655 and 670°, resp. Except for these, the compds. are very H_2O-sensitive. X-ray diffraction data and d. detns. suggest that several of the compds. are isotypic with each other and probably with AlOCl. The chalcogenide halides of Al, Ga, In, and Tl are compared. Richard H. Jaquith

+1

C.A. 1963. 58. 13

13414 de

V 6143 1967

GaDF (ΔH_f, ΔH нагревания)

Ga^+, GaF^+, GaF_2^+, Ga^+, GaF^+, GaF_2^+, $GaDF^+$

(A.P.)

Irnbor K.F., Margrave J.L.,

J Inorg. and Nucl. Chem., 1967, 29, N10,

2649-2650

РЖХ, 1968, 18595 M, HO

6a OF(2) 10m. 22605 1971

Ngai L. H., Stafford F. E.,

M. n.,
Kp.;

Adv. High Temp. Chem.,
1971, 3, 213–270.